E·XFL



Welcome to E-XFL.COM

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	·
Total RAM Bits	36864
Number of I/O	151
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p250-2pqg208

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3 device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system powerup (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3 FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based ProASIC3 devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3 devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3 device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3 devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3 flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3 FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based ProASIC3 devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3 devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3 devices also have low dynamic power consumption to further maximize power savings.



Table 2-9 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard Plus I/O Banks

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (µW/MHz) ²
2.5 V LVCMOS	2.5	-	5.14
1.8 V LVCMOS	1.8	-	2.13
1.5 V LVCMOS (JESD8-11)	1.5	-	1.48
3.3 V PCI	3.3	-	18.13
3.3 V PCI-X	3.3	_	18.13

Notes:

- 1. PDC2 is the static power (where applicable) measured on VMV.
- 2. PAC9 is the total dynamic power measured on VCC and VMV.
- 3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Table 2-10 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard I/O Banks

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (µW/MHz) ²
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	-	17.24
3.3 V LVCMOS Wide Range ³	3.3	-	17.24
2.5 V LVCMOS	2.5	-	5.19
1.8 V LVCMOS	1.8	-	2.18
1.5 V LVCMOS (JESD8-11)	1.5	-	1.52

Notes:

1. PDC2 is the static power (where applicable) measured on VMV.

2. PAC9 is the total dynamic power measured on VCC and VMV.

3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Power Consumption of Various Internal Resources

Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices

			Device	Specif	ic Dyna (µW/M		ontribu	tions	
Parameter	Definition	A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PAC1	Clock contribution of a Global Rib	14.50	12.80	12.80	11.00	11.00	9.30	9.30	9.30
PAC2	Clock contribution of a Global Spine	2.48	1.85	1.35	1.58	0.81	0.81	0.41	0.41
PAC3	Clock contribution of a VersaTile row		•		0.8	1			
PAC4	Clock contribution of a VersaTile used as a sequential module				0.1	2			
PAC5	First contribution of a VersaTile used as a sequential module	0.07							
PAC6	Second contribution of a VersaTile used as a sequential module	0.29							
PAC7	Contribution of a VersaTile used as a combinatorial Module				0.2	9			
PAC8	Average contribution of a routing net				0.7	0			
PAC9	Contribution of an I/O input pin (standard dependent)		See	Table 2 Table		age 2-7 1 page 2		gh	
PAC10	Contribution of an I/O output pin (standard dependent)		See	Table 2 Table 2		page 2- page 2		gh	
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic contribution for PLL				2.6	0			

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.



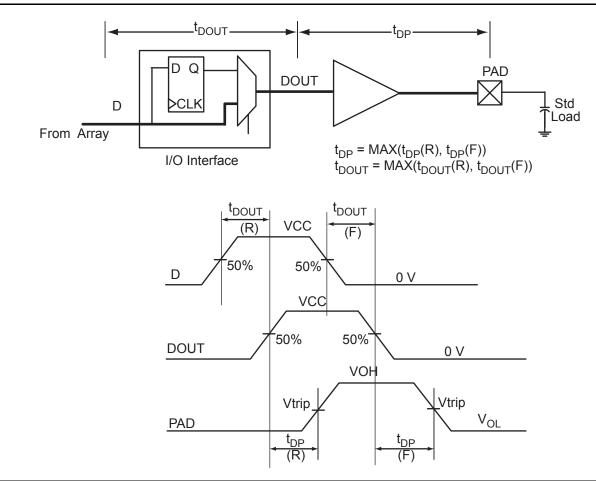


Figure 2-5 • Output Buffer Model and Delays (Example)



Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings

-2 Speed Grade, Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst Case VCC = 1.425 V, Worst-Case VCCI (per standard)

Standard Plus I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor	t _{DOUT} (ns)	t _{DP} (ns)	t _{DIN} (ns)	t _{PY} (ns)	t _{EOUT} (ns)	t _{ZL} (ns)	t _{ZH} (ns)	t _{LZ} (ns)	t _{HZ} (ns)	t _{ZLS} (ns)	t _{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	35	-	0.45	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns
3.3 V LVCMOS Wide Range ²	100 µA	12 mA	High	35	_	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns
2.5 V LVCMOS	12 mA	12 mA	High	35	_	0.45	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns
1.8 V LVCMOS	8 mA	8 mA	High	35	-	0.45	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns
1.5 V LVCMOS	4 mA	4 mA	High	35	-	0.45	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns
3.3 V PCI	Per PCI spec	-	High	10	25 ⁴	0.45	1.72	0.03	0.64	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns
3.3 V PCI-X	Per PCI-X spec	-	High	10	25 ⁴	0.45	1.72	0.03	0.62	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-64 for connectivity. This resistor is not required during normal operation.

Table 2-55 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Standard I/O Banks

		1										
Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t _{dout}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zн}	t _{LZ}	t _{HZ}	Units
100 µA	2 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		-1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		-2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 µA	4 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		-1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		-2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 µA	6 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		-1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		-2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns
100 µA	8 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		-1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		-2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \ \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



Table 2-58 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

2.5 V LVCMOS	v	VIL		VIH		VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max., V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.7	1.7	3.6	0.7	1.7	2	2	16	18	10	10
4 mA	-0.3	0.7	1.7	3.6	0.7	1.7	4	4	16	18	10	10
6 mA	-0.3	0.7	1.7	3.6	0.7	1.7	6	6	32	37	10	10
8 mA	-0.3	0.7	1.7	3.6	0.7	1.7	8	8	32	37	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

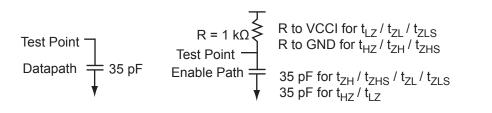


Figure 2-8 • AC Loading

Table 2-59 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	2.5	1.2	35

Note: *Measuring point = Vtrip. See Table 2-22 on page 2-22 for a complete table of trip points.



DDR Module Specifications

Input DDR Module

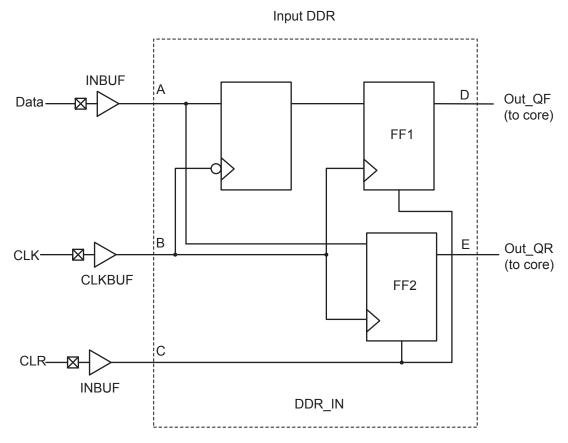


Figure 2-20 • Input DDR Timing Model

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t _{DDRICLKQ1}	Clock-to-Out Out_QR	B, D
t _{DDRICLKQ2}	Clock-to-Out Out_QF	B, E
t _{DDRISUD}	Data Setup Time of DDR input	A, B
t _{DDRIHD}	Data Hold Time of DDR input	A, B
t _{DDRICLR2Q1}	Clear-to-Out Out_QR	C, D
t _{DDRICLR2Q2}	Clear-to-Out Out_QF	C, E
t _{DDRIREMCLR}	Clear Removal	С, В
t _{DDRIRECCLR}	Clear Recovery	C, B



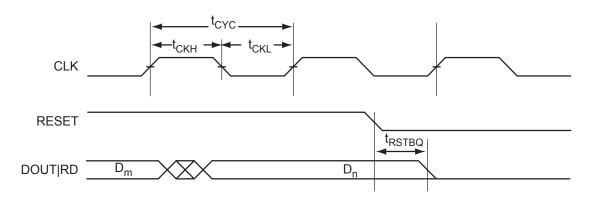


Figure 2-35 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18.



Parameter	Description	-2	-1	Std.	Units
t _{AS}	Address setup time	0.25	0.28	0.33	ns
t _{AH}	Address hold time	0.00	0.00	0.00	ns
t _{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t _{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t _{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t _{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t _{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t _{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t _{C2CRWH} 1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t _{C2CWRH} 1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t _{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
t _{REMRSTB}	RESET removal	0.29	0.33	0.38	ns
t _{RECRSTB}	RESET recovery	1.50	1.71	2.01	ns
t _{MPWRSTB}	RESET minimum pulse width	0.21	0.24	0.29	ns
t _{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F _{MAX}	Maximum frequency	310	272	231	MHz

Table 2-117 • RAM512X18

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



Table 2-121 • A3P250 FIFO 1k×4 Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	-2	-1	Std.	Units
t _{ENS}	REN, WEN Setup Time	4.05	4.61	5.42	ns
t _{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t _{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t _{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t _{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t _{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t _{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t _{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t _{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t _{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t _{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t _{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t _{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t _{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t _{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t _{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t _{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t _{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F _{MAX}	Maximum Frequency for FIFO	310	272	231	MHz



FG144				
Pin Number	A3P1000 Function			
K1	GEB0/IO189NDB3			
K2	GEA1/IO188PDB3			
K3	GEA0/IO188NDB3			
K4	GEA2/IO187RSB2			
K5	IO169RSB2			
K6	IO152RSB2			
K7	GND			
K8	IO117RSB2			
K9	GDC2/IO116RSB2			
K10	GND			
K11	GDA0/IO113NDB1			
K12	GDB0/IO112NDB1			
L1	GND			
L2	VMV3			
L3	GEB2/IO186RSB2			
L4	IO172RSB2			
L5	VCCIB2			
L6	IO153RSB2			
L7	IO144RSB2			
L8	IO140RSB2			
L9	TMS			
L10	VJTAG			
L11	VMV2			
L12	TRST			
M1	GNDQ			
M2	GEC2/IO185RSB2			
M3	IO173RSB2			
M4	IO168RSB2			
M5	IO161RSB2			
M6	IO156RSB2			
M7	IO145RSB2			
M8	IO141RSB2			
M9	TDI			
M10	VCCIB2			
M11	VPUMP			
M12	GNDQ			



	FG256		FG256	FG256	
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
A1	GND	C5	GAC0/IO04RSB0	E9	IO24RSB0
A2	GAA0/IO00RSB0	C6	GAC1/IO05RSB0	E10	VCCIB0
A3	GAA1/IO01RSB0	C7	IO13RSB0	E11	VCCIB0
A4	GAB0/IO02RSB0	C8	IO17RSB0	E12	VMV1
A5	IO07RSB0	C9	IO22RSB0	E13	GBC2/IO43PDB1
A6	IO10RSB0	C10	IO27RSB0	E14	IO46RSB1
A7	IO11RSB0	C11	IO31RSB0	E15	NC
A8	IO15RSB0	C12	GBC0/IO35RSB0	E16	IO45PDB1
A9	IO20RSB0	C13	IO34RSB0	F1	IO113NDB3
A10	IO25RSB0	C14	NC	F2	IO112PPB3
A11	IO29RSB0	C15	IO42NPB1	F3	NC
A12	IO33RSB0	C16	IO44PDB1	F4	IO115VDB3
A13	GBB1/IO38RSB0	D1	IO114VDB3	F5	VCCIB3
A14	GBA0/IO39RSB0	D2	IO114UDB3	F6	GND
A15	GBA1/IO40RSB0	D3	GAC2/IO116UDB3	F7	VCC
A16	GND	D4	NC	F8	VCC
B1	GAB2/IO117UDB3	D5	GNDQ	F9	VCC
B2	GAA2/IO118UDB3	D6	IO08RSB0	F10	VCC
B3	NC	D7	IO14RSB0	F11	GND
B4	GAB1/IO03RSB0	D8	IO18RSB0	F12	VCCIB1
B5	IO06RSB0	D9	IO23RSB0	F13	IO43NDB1
B6	IO09RSB0	D10	IO28RSB0	F14	NC
B7	IO12RSB0	D11	IO32RSB0	F15	IO47PPB1
B8	IO16RSB0	D12	GNDQ	F16	IO45NDB1
B9	IO21RSB0	D13	NC	G1	IO111NDB3
B10	IO26RSB0	D14	GBB2/IO42PPB1	G2	IO111PDB3
B11	IO30RSB0	D15	NC	G3	IO112NPB3
B12	GBC1/IO36RSB0	D16	IO44NDB1	G4	GFC1/IO110PPB3
B13	GBB0/IO37RSB0	E1	IO113PDB3	G5	VCCIB3
B14	NC	E2	NC	G6	VCC
B15	GBA2/IO41PDB1	E3	IO116VDB3	G7	GND
B16	IO41NDB1	E4	IO115UDB3	G8	GND
C1	IO117VDB3	E5	VMV0	G9	GND
C2	IO118VDB3	E6	VCCIB0	G10	GND
C3	NC	E7	VCCIB0	G11	VCC
C4	NC	E8	IO19RSB0	G12	VCCIB1

🌜 Microsemi.

Package Pin Assignments

	FG256		FG256		FG256
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
G13	GCC1/IO48PPB1	K1	GFC2/IO105PDB3	M5	VMV3
G14	IO47NPB1	K2	IO107NPB3	M6	VCCIB2
G15	IO54PDB1	K3	IO104PPB3	M7	VCCIB2
G16	IO54NDB1	K4	NC	M8	NC
H1	GFB0/IO109NPB3	K5	VCCIB3	M9	IO74RSB2
H2	GFA0/IO108NDB3	K6	VCC	M10	VCCIB2
H3	GFB1/IO109PPB3	K7	GND	M11	VCCIB2
H4	VCOMPLF	K8	GND	M12	VMV2
H5	GFC0/IO110NPB3	K9	GND	M13	NC
H6	VCC	K10	GND	M14	GDB1/IO59UPB1
H7	GND	K11	VCC	M15	GDC1/IO58UDB1
H8	GND	K12	VCCIB1	M16	IO56NDB1
H9	GND	K13	IO52NPB1	N1	IO103NDB3
H10	GND	K14	IO55RSB1	N2	IO101PPB3
H11	VCC	K15	IO53NPB1	N3	GEC1/IO100PPB3
H12	GCC0/IO48NPB1	K16	IO51NDB1	N4	NC
H13	GCB1/IO49PPB1	L1	IO105NDB3	N5	GNDQ
H14	GCA0/IO50NPB1	L2	IO104NPB3	N6	GEA2/IO97RSB2
H15	NC	L3	NC	N7	IO86RSB2
H16	GCB0/IO49NPB1	L4	IO102RSB3	N8	IO82RSB2
J1	GFA2/IO107PPB3	L5	VCCIB3	N9	IO75RSB2
J2	GFA1/IO108PDB3	L6	GND	N10	IO69RSB2
J3	VCCPLF	L7	VCC	N11	IO64RSB2
J4	IO106NDB3	L8	VCC	N12	GNDQ
J5	GFB2/IO106PDB3	L9	VCC	N13	NC
J6	VCC	L10	VCC	N14	VJTAG
J7	GND	L11	GND	N15	GDC0/IO58VDB1
J8	GND	L12	VCCIB1	N16	GDA1/IO60UDB1
J9	GND	L13	GDB0/IO59VPB1	P1	GEB1/IO99PDB3
J10	GND	L14	IO57VDB1	P2	GEB0/IO99NDB3
J11	VCC	L15	IO57UDB1	P3	NC
J12	GCB2/IO52PPB1	L16	IO56PDB1	P4	NC
J13	GCA1/IO50PPB1	M1	IO103PDB3	P5	IO92RSB2
J14	GCC2/IO53PPB1	M2	NC	P6	IO89RSB2
J15	NC	M3	IO101NPB3	P7	IO85RSB2
J16	GCA2/IO51PDB1	M4	GEC0/IO100NPB3	P8	IO81RSB2

🌜 Microsemi.

Package Pin Assignments

	FG484		FG484		FG484
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
A1	GND	B15	IO63RSB0	D7	GAB0/IO02RSB0
A2	GND	B16	IO66RSB0	D8	IO16RSB0
A3	VCCIB0	B17	IO68RSB0	D9	IO22RSB0
A4	IO07RSB0	B18	IO70RSB0	D10	IO28RSB0
A5	IO09RSB0	B19	NC	D11	IO35RSB0
A6	IO13RSB0	B20	NC	D12	IO45RSB0
A7	IO18RSB0	B21	VCCIB1	D13	IO50RSB0
A8	IO20RSB0	B22	GND	D14	IO55RSB0
A9	IO26RSB0	C1	VCCIB3	D15	IO61RSB0
A10	IO32RSB0	C2	IO220PDB3	D16	GBB1/IO75RSB0
A11	IO40RSB0	C3	NC	D17	GBA0/IO76RSB0
A12	IO41RSB0	C4	NC	D18	GBA1/IO77RSB0
A13	IO53RSB0	C5	GND	D19	GND
A14	IO59RSB0	C6	IO10RSB0	D20	NC
A15	IO64RSB0	C7	IO14RSB0	D21	NC
A16	IO65RSB0	C8	VCC	D22	NC
A17	IO67RSB0	C9	VCC	E1	IO219NDB3
A18	IO69RSB0	C10	IO30RSB0	E2	NC
A19	NC	C11	IO37RSB0	E3	GND
A20	VCCIB0	C12	IO43RSB0	E4	GAB2/IO224PDB3
A21	GND	C13	NC	E5	GAA2/IO225PDB3
A22	GND	C14	VCC	E6	GNDQ
B1	GND	C15	VCC	E7	GAB1/IO03RSB0
B2	VCCIB3	C16	NC	E8	IO17RSB0
B3	NC	C17	NC	E9	IO21RSB0
B4	IO06RSB0	C18	GND	E10	IO27RSB0
B5	IO08RSB0	C19	NC	E11	IO34RSB0
B6	IO12RSB0	C20	NC	E12	IO44RSB0
B7	IO15RSB0	C21	NC	E13	IO51RSB0
B8	IO19RSB0	C22	VCCIB1	E14	IO57RSB0
B9	IO24RSB0	D1	IO219PDB3	E15	GBC1/IO73RSB0
B10	IO31RSB0	D2	IO220NDB3	E16	GBB0/IO74RSB0
B11	IO39RSB0	D3	NC	E17	IO71RSB0
B12	IO48RSB0	D4	GND	E18	GBA2/IO78PDB1
B13	IO54RSB0	D5	GAA0/IO00RSB0	E19	IO81PDB1
B14	IO58RSB0	D6	GAA1/IO01RSB0	E20	GND

🌜 Microsemi.

Package Pin Assignments

	FG484		FG484	FG484		
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	
K19	IO88NDB1	M11	GND	P3	IO199NDB3	
K20	IO94NPB1	M12	GND	P4	IO202NDB3	
K21	IO98NDB1	M13	GND	P5	IO202PDB3	
K22	IO98PDB1	M14	VCC	P6	IO196PPB3	
L1	NC	M15	GCB2/IO95PPB1	P7	IO193PPB3	
L2	IO200PDB3	M16	GCA1/IO93PPB1	P8	VCCIB3	
L3	IO210NPB3	M17	GCC2/IO96PPB1	P9	GND	
L4	GFB0/IO208NPB3	M18	IO100PPB1	P10	VCC	
L5	GFA0/IO207NDB3	M19	GCA2/IO94PPB1	P11	VCC	
L6	GFB1/IO208PPB3	M20	IO101PPB1	P12	VCC	
L7	VCOMPLF	M21	IO99PPB1	P13	VCC	
L8	GFC0/IO209NPB3	M22	NC	P14	GND	
L9	VCC	N1	IO201NDB3	P15	VCCIB1	
L10	GND	N2	IO201PDB3	P16	GDB0/IO112NPB1	
L11	GND	N3	NC	P17	IO106NDB1	
L12	GND	N4	GFC2/IO204PDB3	P18	IO106PDB1	
L13	GND	N5	IO204NDB3	P19	IO107PDB1	
L14	VCC	N6	IO203NDB3	P20	NC	
L15	GCC0/IO91NPB1	N7	IO203PDB3	P21	IO104PDB1	
L16	GCB1/IO92PPB1	N8	VCCIB3	P22	IO103NDB1	
L17	GCA0/IO93NPB1	N9	VCC	R1	NC	
L18	IO96NPB1	N10	GND	R2	IO197PPB3	
L19	GCB0/IO92NPB1	N11	GND	R3	VCC	
L20	IO97PDB1	N12	GND	R4	IO197NPB3	
L21	IO97NDB1	N13	GND	R5	IO196NPB3	
L22	IO99NPB1	N14	VCC	R6	IO193NPB3	
M1	NC	N15	VCCIB1	R7	GEC0/IO190NPB3	
M2	IO200NDB3	N16	IO95NPB1	R8	VMV3	
M3	IO206NDB3	N17	IO100NPB1	R9	VCCIB2	
M4	GFA2/IO206PDB3	N18	IO102NDB1	R10	VCCIB2	
M5	GFA1/IO207PDB3	N19	IO102PDB1	R11	IO147RSB2	
M6	VCCPLF	N20	NC	R12	IO136RSB2	
M7	IO205NDB3	N21	IO101NPB1	R13	VCCIB2	
M8	GFB2/IO205PDB3	N22	IO103PDB1	R14	VCCIB2	
M9	VCC	P1	NC	R15	VMV2	
M10	GND	P2	IO199PDB3	R16	IO110NDB1	



Datasheet Information

Revision	Changes	Page
Revision 11 (March 2012)	Note indicating that A3P015 is not recommended for new designs has been added. The "Devices Not Recommended For New Designs" section is new (SAR 36760).	I to IV
	The following sentence was removed from the Advanced Architecture section: "In addition, extensive on-chip programming circuitry allows for rapid, single- voltage (3.3 V) programming of IGLOO devices via an IEEE 1532 JTAG interface" (SAR 34687).	NA
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—PCLOCK" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the <i>ProASIC3 FPGA Fabric User's Guide</i> (SAR 34734).	2-12
	Figure 2-4 • Input Buffer Timing Model and Delays (Example) has been modified for the DIN waveform; the Rise and Fall time label has been changed to tDIN (35430).	2-16
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34883).	2-32
	Added values for minimum pulse width and removed the FRMAX row from Table 2-107 through Table 2-114 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SARs 37279, 29269).	2-85



Datasheet Information

Revision	Changes	Page
v2.0 (April 2007)	In the "Packaging Tables", Ambient was deleted.	ii
	The timing characteristics tables were updated.	N/A
	The "PLL Macro" section was updated to add information on the VCO and PLL outputs during power-up.	2-15
	The "PLL Macro" section was updated to include power-up information.	2-15
	Table 2-11 • ProASIC3 CCC/PLL Specification was updated.	2-29
	Figure 2-19 • Peak-to-Peak Jitter Definition is new.	2-18
	The "SRAM and FIFO" section was updated with operation and timing requirement information.	2-21
	The "RESET" section was updated with read and write information.	2-25
	The "RESET" section was updated with read and write information.	2-25
	The "Introduction" in the "Advanced I/Os" section was updated to include information on input and output buffers being disabled.	2-28
	PCI-X 3.3 V was added to Table 2-11 • VCCI Voltages and Compatible Standards.	2-29
	In the Table 2-15 • Levels of Hot-Swap Support, the ProASIC3 compliance descriptions were updated for levels 3 and 4.	2-34
	Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices was updated.	2-64
	Notes 3, 4, and 5 were added to Table 2-17 \cdot Comparison Table for 5 V–Compliant Receiver Scheme. 5 x 52.72 was changed to 52.7 and the Maximum current was updated from 4 x 52.7 to 5 x 52.7.	2-40
	The "VCCPLF PLL Supply Voltage" section was updated.	2-50
	The "VPUMP Programming Supply Voltage" section was updated.	2-50
	The "GL Globals" section was updated to include information about direct input into quadrant clocks.	2-51
	V _{JTAG} was deleted from the "TCK Test Clock" section.	2-51
	In Table 2-22 • Recommended Tie-Off Values for the TCK and TRST Pins, TSK was changed to TCK in note 2. Note 3 was also updated.	2-51
	Ambient was deleted from Table 3-2 • Recommended Operating Conditions. VPUMP programming mode was changed from "3.0 to 3.6" to "3.15 to 3.45".	3-2
	Note 3 is new in Table 3-4 • Overshoot and Undershoot Limits (as measured on quiet I/Os)1.	3-2
	In EQ 3-2, 150 was changed to 110 and the result changed from 3.9 to 1.951.	3-5
	Table 3-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	3-6
	Table 3-5 • Package Thermal Resistivities was updated.	3-5
	Table 3-14 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings (Advanced) and Table 3-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions (Standard Plus) were updated.	3-17 to 3- 17



Revision	Changes	Page
v2.0 (continued)	Table 3-20 • Summary of I/O Timing Characteristics—Software Default Settings(Advanced) and Table 3-21 • Summary of I/O Timing Characteristics—SoftwareDefault Settings (Standard Plus) were updated.	3-20 to 3-20
	Table 3-11 • Different Components Contributing to Dynamic Power Consumptionin ProASIC3 Devices was updated.	3-9
	Table 3-24 • I/O Output Buffer Maximum Resistances1 (Advanced) and Table 3-25 • I/O Output Buffer Maximum Resistances1 (Standard Plus) were updated.	3-22 to 3-22
	Table 3-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions was updated.	3-18
	Table 3-28 • I/O Short Currents IOSH/IOSL (Advanced) and Table 3-29 • I/O Short Currents IOSH/IOSL (Standard Plus) were updated.	3-24 to 3-26
	The note in Table 3-32 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-27
	Figure 3-33 • Write Access After Write onto Same Address, Figure 3-34 • Read Access After Write onto Same Address, and Figure 3-35 • Write Access After Read onto Same Address are new.	3-82 to 3-84
	Figure 3-43 • Timing Diagram was updated.	3-96
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3P030 "132-Pin QFN" table is new.	4-2
	The A3P060 "132-Pin QFN" table is new.	4-4
	The A3P125 "132-Pin QFN" table is new.	4-6
	The A3P250 "132-Pin QFN" table is new.	4-8
	The A3P030 "100-Pin VQFP" table is new.	4-11
Advance v0.7 (January 2007)	In the "I/Os Per Package" table, the I/O numbers were added for A3P060, A3P125, and A3P250. The A3P030-VQ100 I/O was changed from 79 to 77.	ii
Advance v0.6 (April 2006)	The term flow-through was changed to pass-through.	N/A
	Table 1 was updated to include the QN132.	ii
	The "I/Os Per Package" table was updated with the QN132. The footnotes were also updated. The A3P400-FG144 I/O count was updated.	ii
	"Automotive ProASIC3 Ordering Information" was updated with the QN132.	iii
	"Temperature Grade Offerings" was updated with the QN132.	iii
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-7 • Efficient Long-Line Resources was updated.	2-7
	The footnotes in Figure 2-15 • Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT were updated.	2-16
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21



Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "ProASIC3 Device Status" table on page IV, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Unmarked (production)

This version contains information that is considered to be final.

Export Administration Regulations (EAR)

The products described in this document are subject to the Export Administration Regulations (EAR). They could require an approved export license prior to export from the United States. An export includes release of product or disclosure of technology to a foreign national inside or outside the United States.

Safety Critical, Life Support, and High-Reliability Applications Policy

The products described in this advance status document may not have completed the Microsemi qualification process. Products may be amended or enhanced during the product introduction and qualification process, resulting in changes in device functionality or performance. It is the responsibility of each customer to ensure the fitness of any product (but especially a new product) for a particular purpose, including appropriateness for safety-critical, life-support, and other high-reliability applications. Consult the Microsemi SoC Products Group Terms and Conditions for specific liability exclusions relating to life-support applications. A reliability report covering all of the SoC Products Group's products is available at http://www.microsemi.com/soc/documents/ORT_Report.pdf. Microsemi also offers a variety of enhanced qualification and lot acceptance screening procedures. Contact your local sales office for additional reliability information.